

S/N 08/903,453

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT

Applicant: Leonard Forbes et al.

Examiner: George C. Eckert II

Serial No.: 08/903,453

Group Art Unit: 2815

Filed: July 29, 1997

Docket: 303.378US1

Title: CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS

24/Amend E
R. Tyson
3/10/01



AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

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TECHNOLOGY CENTER 2800A

In response to the Office Action dated 24 October 2000, please amend the application as follows.

This response is accompanied by a Petition, as well as the appropriate fee, to obtain a one-month extension of the period for responding to the Office action, thereby moving the deadline for response from 24 January 2001 to 24 February 2001.

IN THE CLAIMS

Please amend the claims as follows:

1. [Amended] An integrated circuit field effect transistor [having] comprising an amorphous carburized silicon layer gate insulator that was grown on a substrate.
2. [Amended] An integrated circuit field effect transistor comprising:
a source and a drain separated by a channel supported by a semiconductor substrate;
a gate supported by the substrate and extending between the source and drain above the channel; and
an insulative amorphous layer of carburized silicon [formed] grown on the channel and located between the channel and the gate.
3. [Amended] An integrated circuit memory device supported by a semiconductor substrate, the device comprising:
a source and a drain separated by a channel supported by a semiconductor substrate;
a floating gate supported by the substrate and extending between the source and drain

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02 FC:103

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